

# B772 HEF:200-300

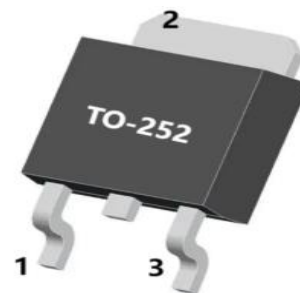
## PNP SILICON TRANSISTOR

### ■ GENERAL DESCRIPTION

The 2SB772 is a medium power low voltage transistor, designed for audio power amplifier, DC-DC converter and voltage regulator.

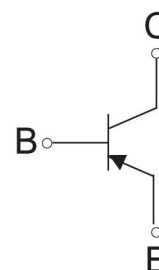
### ■ FEATURES

- \*High current output up to 3A
- \*Low saturation voltage
- \*Complement to 2SD882



1. BASE
2. COLLECTOR
3. EMITTER

Equivalent Circuit



### ■ ABSOLUTE MAXIMUM RATINGS (TA=25°C, unless otherwise specified)

| SYMBOL           | PARAMETER                      |        | VALUE       | UNIT |
|------------------|--------------------------------|--------|-------------|------|
| V <sub>CB0</sub> | Collector-Base Voltage         |        | -40         | V    |
| V <sub>CEO</sub> | Collector-Emitter Voltage      |        | -30         | V    |
| V <sub>EB0</sub> | Emitter-Base Voltage           | TO-252 | -7          | V    |
| I <sub>C</sub>   | Collector Current (DC)         |        | -3          | A    |
| I <sub>CP</sub>  | Collector Current (Pulse)      |        | -7          | A    |
| I <sub>B</sub>   | Base Current                   |        | -0.6        | A    |
| P <sub>C</sub>   | Collector Dissipation          | TO-252 | 1           | W    |
| T <sub>j</sub>   | Operating Junction Temperature |        | +150        | °C   |
| T <sub>stg</sub> | Storage Temperature            |        | -55 to +150 | °C   |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

2. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

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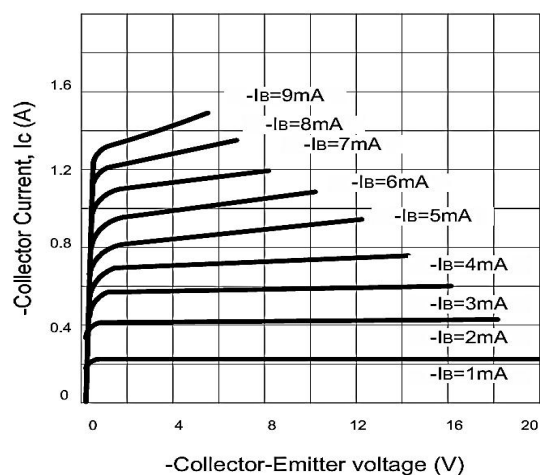
### ■ ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

| PARAMETER                                                       | SYMBOL               | TEST CONDITIONS                                  | MIN | TYP  | MAX  | UNIT |
|-----------------------------------------------------------------|----------------------|--------------------------------------------------|-----|------|------|------|
| Collector-Base Breakdown Voltage                                | V <sub>CBO</sub>     | I <sub>C</sub> =-100μA, I <sub>E</sub> =0        | -40 |      |      | V    |
| Collector-Emitter Breakdown Voltage                             | V <sub>CEO</sub>     | I <sub>C</sub> =-1mA, I <sub>B</sub> =0          | -30 |      |      | V    |
| Emitter-Base Breakdown Voltage                                  | V <sub>EBO</sub>     | I <sub>E</sub> =-100μA, I <sub>C</sub> =0        | -7  |      |      | V    |
| Collector Cut-Off Current                                       | I <sub>CBO</sub>     | V <sub>CB</sub> =-30V, I <sub>E</sub> =0         |     |      | -1   | μA   |
| Collector Cut-Off Current                                       | I <sub>CEO</sub>     | V <sub>CE</sub> =-30V, I <sub>B</sub> =0         |     |      | -1   | μA   |
| Emitter Cut-Off Current                                         | I <sub>EBO</sub>     | V <sub>EB</sub> =-5V, I <sub>C</sub> =0          |     |      | -1   | μA   |
| DC Current Gain (Note)<br>(CLASSIFICATION OF h <sub>FE2</sub> ) | h <sub>FE1</sub>     | V <sub>CE</sub> =-2V, I <sub>C</sub> =-20mA      | 30  | 200  |      |      |
|                                                                 | h <sub>FE2</sub>     | V <sub>CE</sub> =-2V, I <sub>C</sub> =-1A        | 100 |      | 200  |      |
|                                                                 |                      |                                                  | 160 |      | 320  |      |
|                                                                 |                      |                                                  | 200 |      | 400  |      |
| Collector-Emitter Saturation Voltage                            | V <sub>CE(SAT)</sub> | I <sub>C</sub> =-2A, I <sub>B</sub> =-0.2A       |     | -0.3 | -0.5 | V    |
| Base-Emitter Saturation Voltage                                 | V <sub>BE(SAT)</sub> | I <sub>C</sub> =-2A, I <sub>B</sub> =-0.2A       |     | -1.0 | -2.0 | V    |
| Current Gain Bandwidth Product                                  | f <sub>T</sub>       | V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.1A      |     | 80   |      | MHz  |
| Output Capacitance                                              | C <sub>OB</sub>      | V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz |     | 45   |      | pF   |

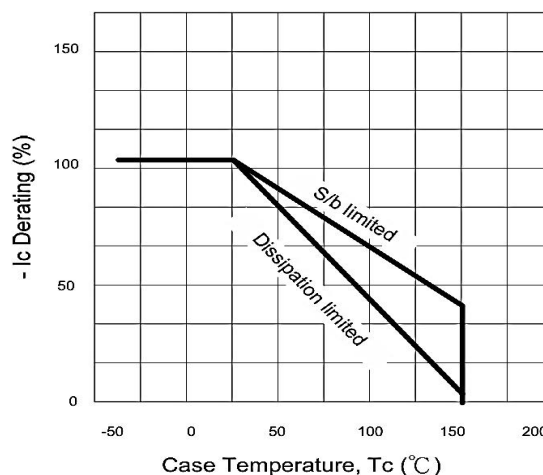
Note: Pulse test: Pw ≤ 300μs, Duty Cycle ≤ 2%

### ■ TYPICAL CHARACTERISTICS

Static Characteristics



Derating Curve of Safe Operating Areas

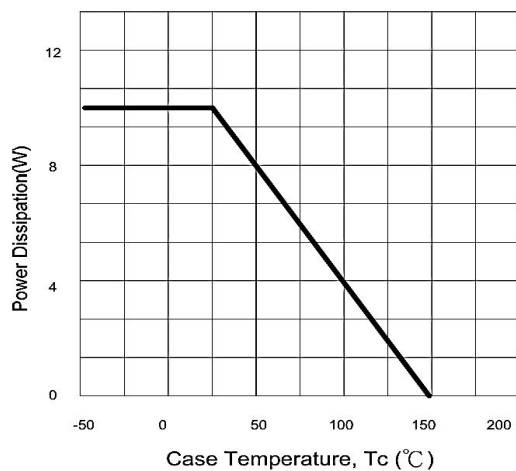


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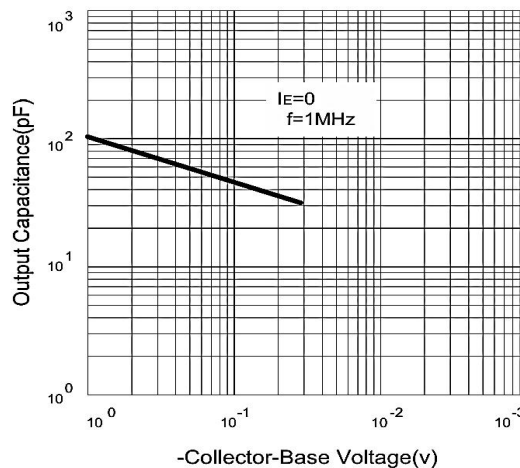
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### ■ TYPICAL CHARACTERISTICS(Con.t)

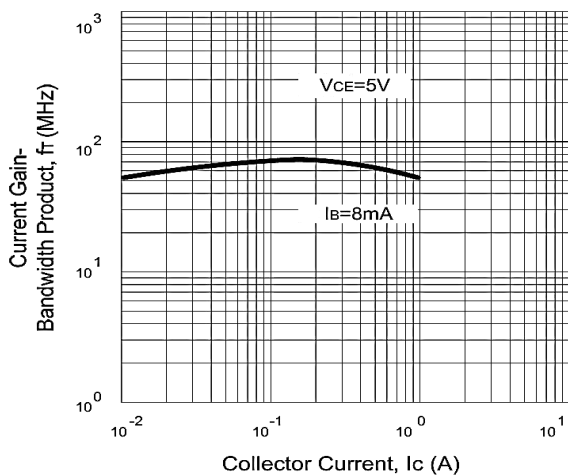
Power Derating



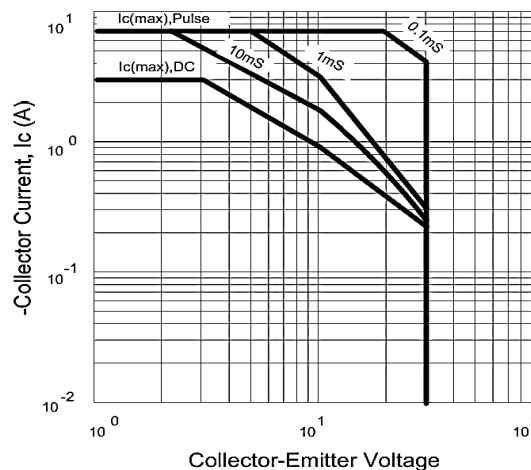
Collector Output Capacitance



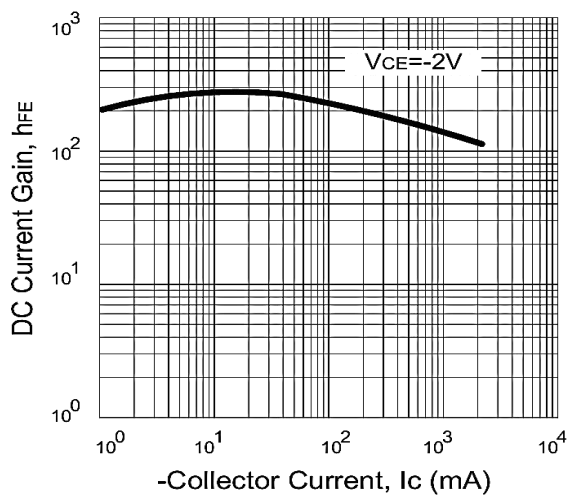
Current Gain-Bandwidth Product



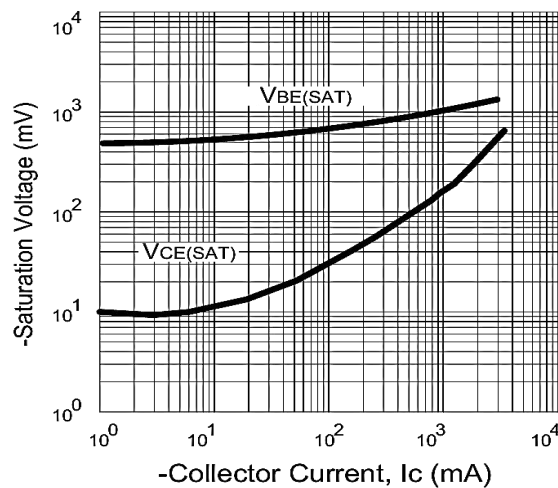
Safe Operating Area



DC Current Gain

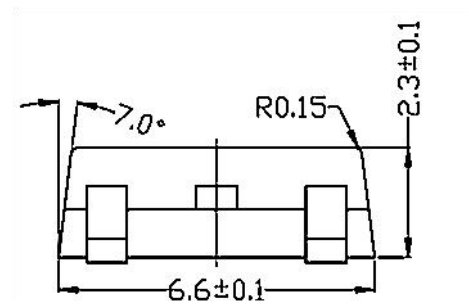


Saturation Voltage





## PNP SILICON TRANSISTOR



| Package version | Reel dimensions<br>$\phi \times H$ (mm) | Per Reel (pcs) | Reels per box | Inner box dimensions<br>$L \times W \times H$ (mm) | Outer box (pcs) | Outer box dimensions<br>$L \times W \times H$ (mm) |
|-----------------|-----------------------------------------|----------------|---------------|----------------------------------------------------|-----------------|----------------------------------------------------|
| T0-252          | $\phi 330 \times 20$                    | 2500           | 2             | 360*340*50                                         | 25000           | 375*375*280                                        |